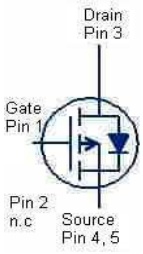
OptiMOS®-P Power-Transistor

Features

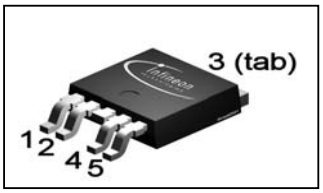
- P-Channel
- Enhancement mode
- Logic level
- 175°C operating temperature
- Avalanche rated
- d*v*/d*t* rated
- High current rating
- Pb-free lead-plating, RoHS compliant

Product Summary

V_{DS}	-30	V
$R_{DS(on),max}$	7	mΩ
I_D	-50	A



PG-TO252-5



Type	Package	Marking	Tape and reel information	Lead Free	Packing
SPD50P03L G	PG-TO252-5	50P03L	1000 pcs / reel	Yes	Non dry

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25 °C[1)]	-50	A
		T_C=100 °C[1)]	-50	
Pulsed drain current	$I_{D,pulse}$	T_C=25 °C	-200	
Avalanche energy, single pulse	E_{AS}	I_D=-50 A, R_{GS}=25 Ω	256	mJ
Reverse diode d*v*/d*t*	d*v*/d*t*	I_D=-50 A, V_{DS}=24 V, d*i*/d*t*=-200 A/µs, $T_{j,max}$=175 °C	-6	kV/µs
Gate source voltage	V_{GS}		±20	V
Power dissipation	P_{tot}	T_C=25 °C	150	W
Operating and storage temperature	T_j, T_{stg}		-55…+175	°C
ESD class HBM			1C	
Soldering temperature			260	
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	1	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint	-	-	75	
		6 cm^2 cooling area[2)]	-	-	50	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=-250 µA	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250 µA	-1	-1.5	-2	
Zero gate voltage drain current	I_{DSS}	V_{DS}=-30 V, V_{GS}=0 V, T_j=25 °C	-	-0.1	-1	µA
		V_{DS}=-30 V, V_{GS}=0 V, T_j=175 °C	-	-10	-100	
Gate-source leakage current	I_{GSS}	V_{GS}=-20 V, V_{DS}=0 V	-	-10	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=-4.5 V, I_D=-30 A	-	8.5	12.5	mΩ
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=-10 V, I_D=-50 A	-	5.7	7.0	
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=-50 A	47	94	-	S

[1)] Current is limited by bondwire; with an R_{thJC}=1 K/W the chip is able to carry 123 A.

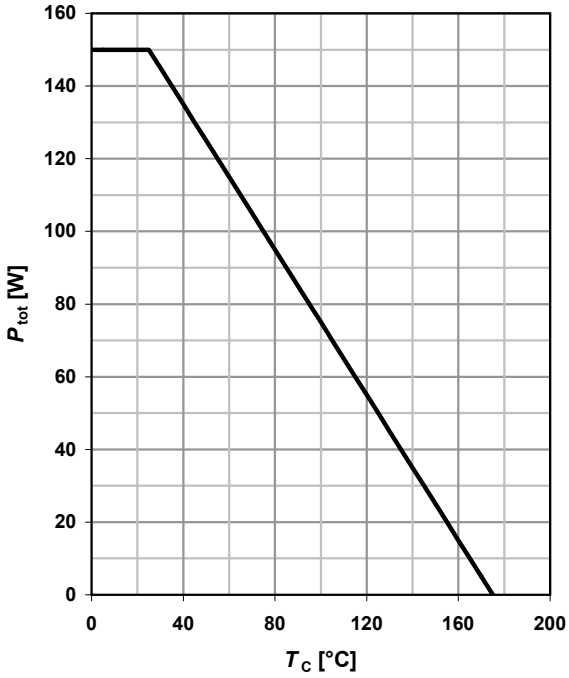
[2)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=-25 V, f=1 MHz	-	4590	6880	pF
Output capacitance	C_{oss}		-	1220	1830	
Reverse transfer capacitance	C_{rss}		-	1000	1500	
Turn-on delay time	$t_{d(on)}$	V_{DD}=-15 V, V_{GS}=-10 V, I_D=-1 A, R_G=6 Ω	-	14.8	22	ns
Rise time	t_r		-	21.7	32	
Turn-off delay time	$t_{d(off)}$		-	139	208	
Fall time	t_f		-	104	156	
Gate Charge Characteristics[3)]						
Gate to source charge	Q_{gs}	V_{DD}=-24 V, I_D=-50 A	-	-14	-19	nC
Gate to drain charge	Q_{gd}		-	-35	-53	
Gate charge total	Q_g	V_{DD}=-24 V, I_D=-50 A, V_{GS}=0 to -10 V	-	-95	-126	
Gate plateau voltage	$V_{plateau}$	V_{DD}=-24 V, I_D=-50 A	-	-3.0	-	V
Reverse Diode						
Diode continous forward current	I_S	T_C=25 °C	-	-	-50	A
Diode pulse current	$I_{S,pulse}$		-	-	-200	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=50 A, T_j=25 °C	-	-1	-1.65	V
Reverse recovery time	t_{rr}	V_R=-15 V, I_F=$\|I_S\|$, di_F/dt=100 A/µs	-	38	47	ns
Reverse recovery charge	Q_{rr}		-	46	57	nC

[3)] See figure 16 for gate charge parameter definition

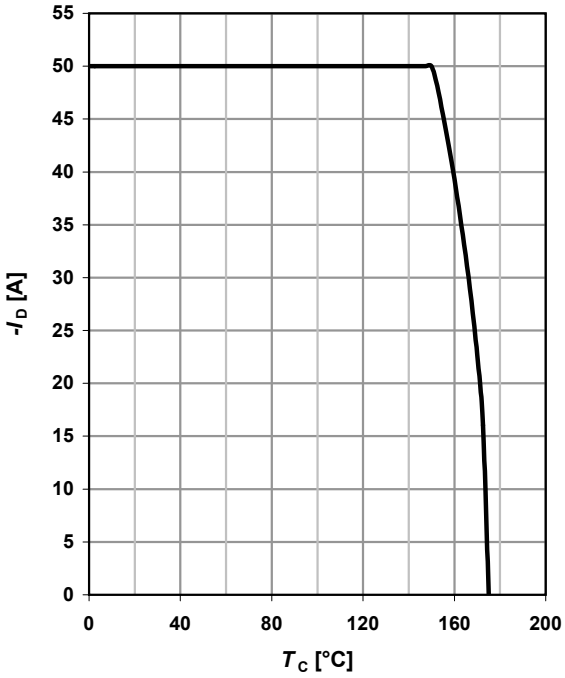
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

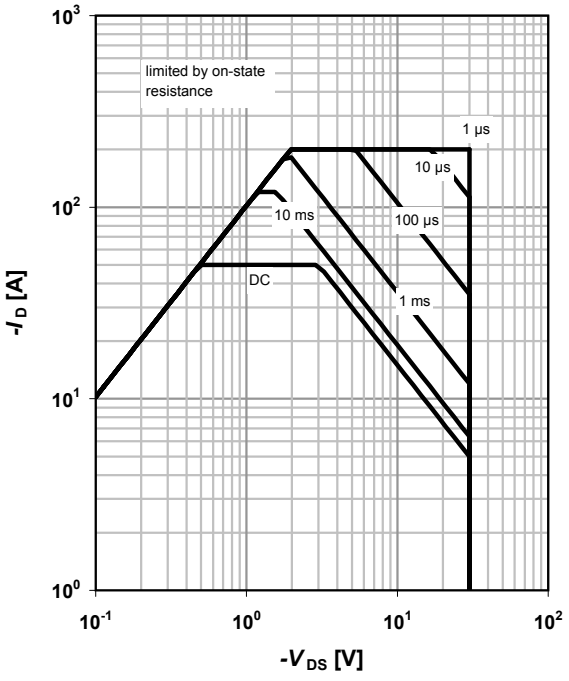
$I_D=f(T_C)$; $|V_{GS}|\geq 10$ V



3 Safe operating area

$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$

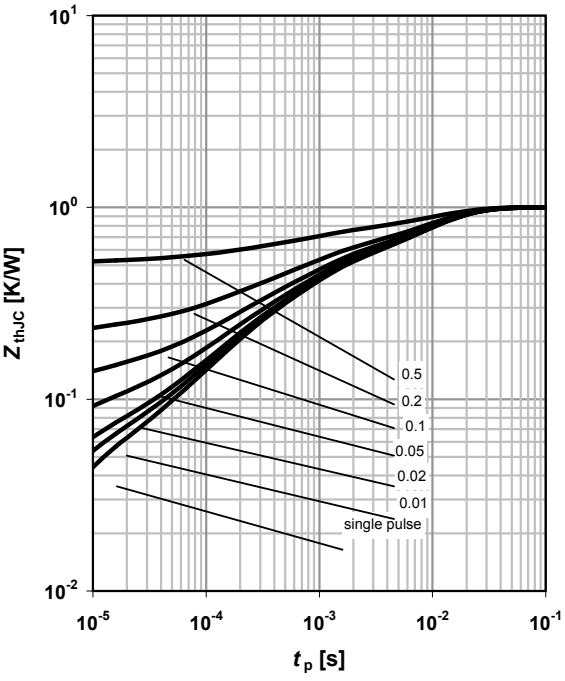
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

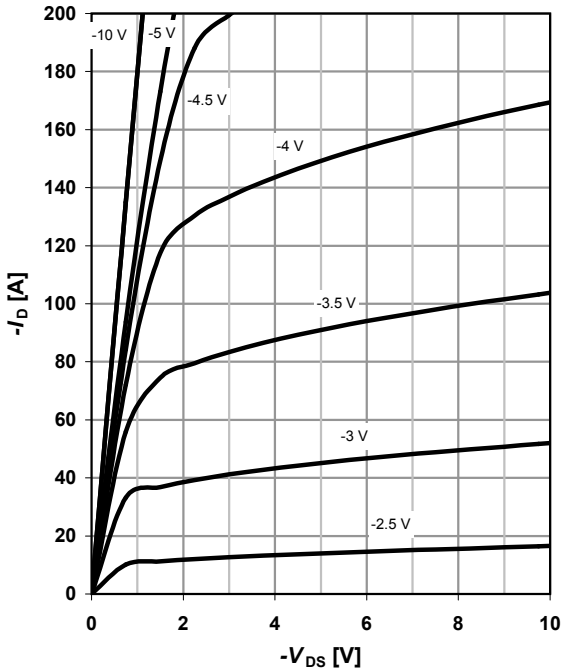
parameter: $D=t_p/T$



5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

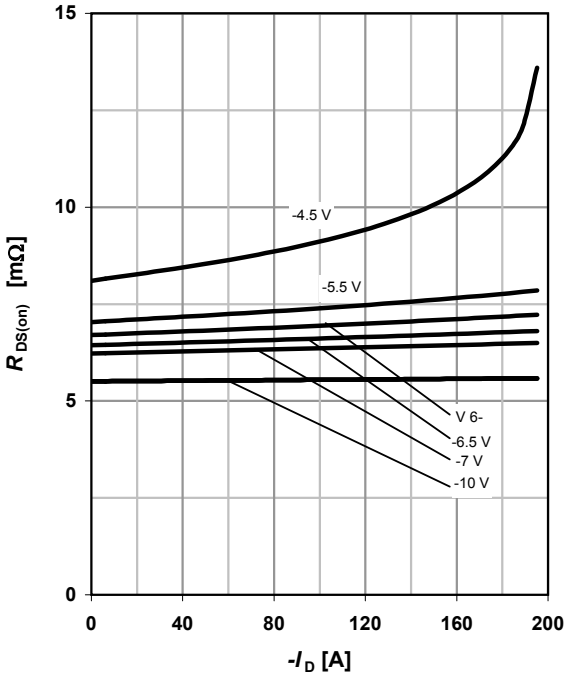
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)}$=f(I_D); T_j=25 °C

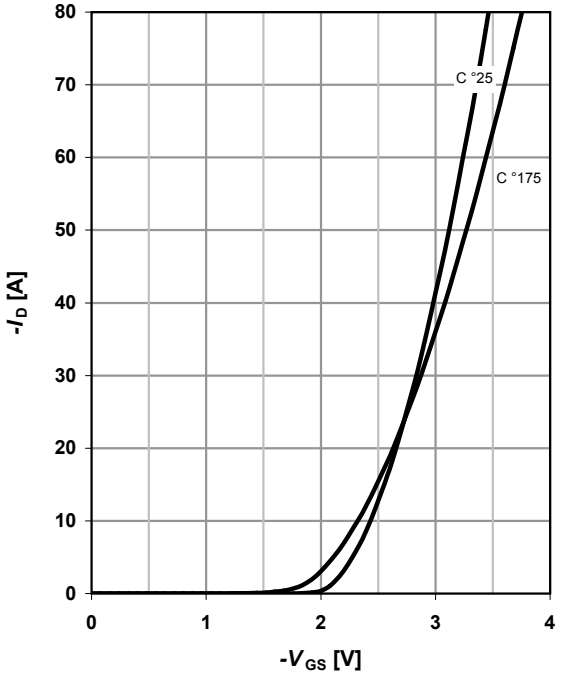
parameter: V_{GS}



7 Typ. transfer characteristics

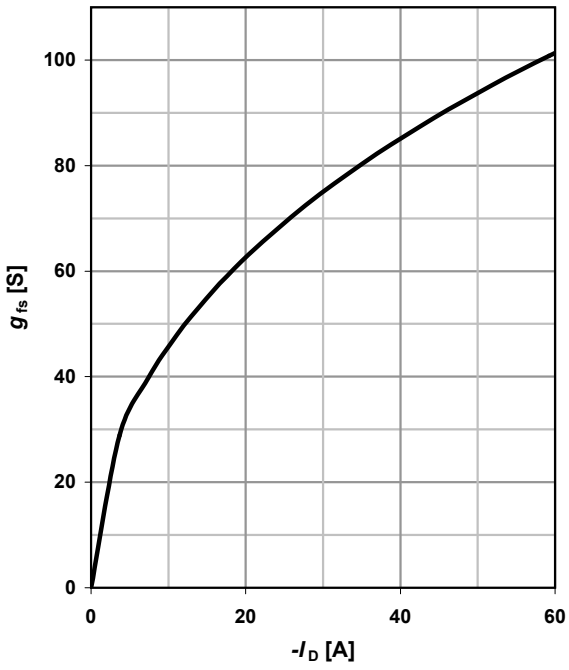
I_D=f(V_{GS}); $|V_{DS}|>2|I_D|R_{DS(on)max}$

parameter: T_j



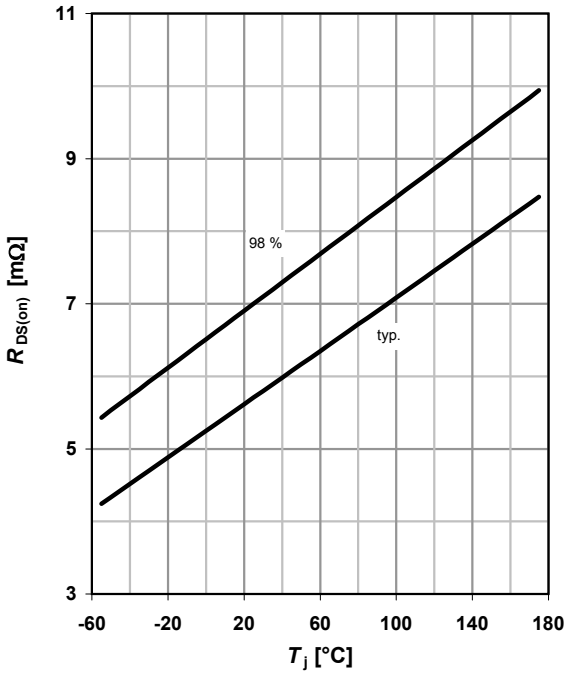
8 Typ. forward transconductance

g_{fs}=f(I_D); T_j=25 °C



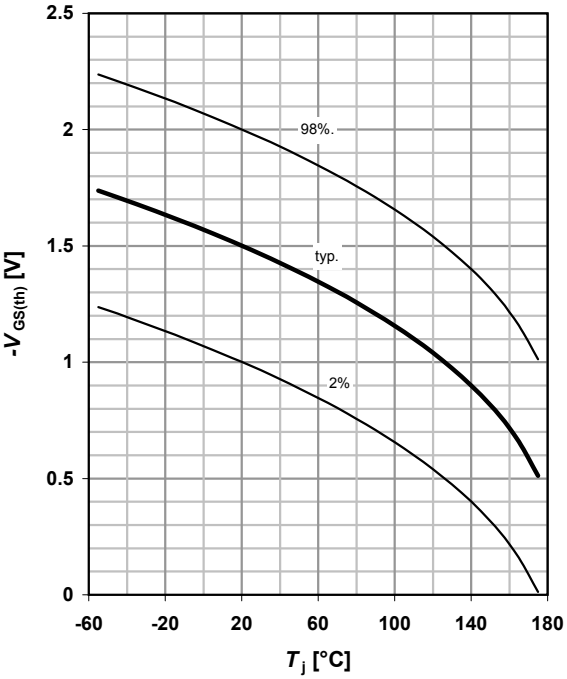
9 Drain-source on-state resistance

$R_{DS(on)}$=f(T_j); I_D=-50 A; V_{GS}=-10 V



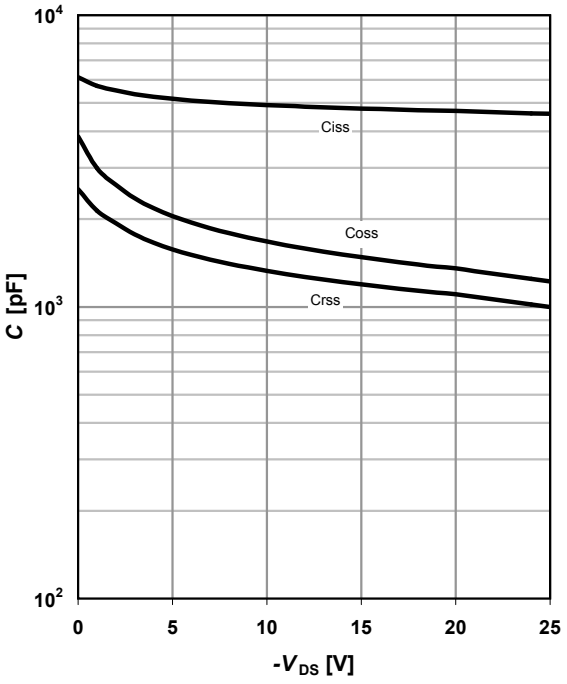
10 Typ. gate threshold voltage

$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}; I_D=-250 µA



11 Typ. capacitances

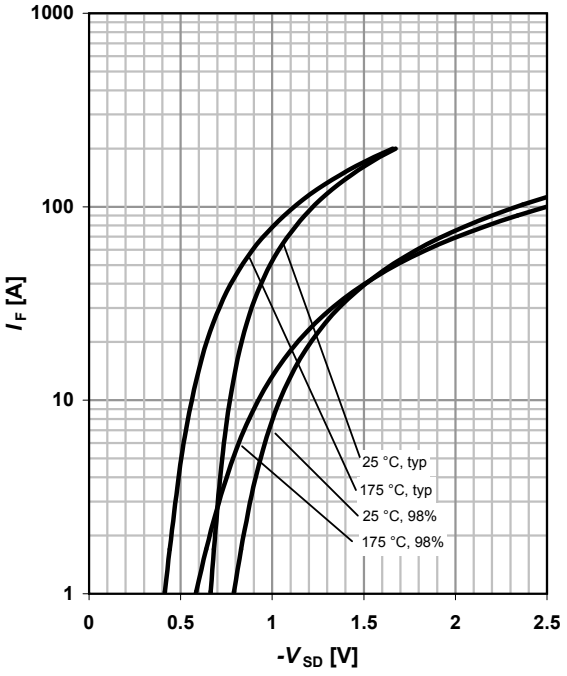
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz



12 Forward characteristics of reverse diode

I_F=f(V_{SD})

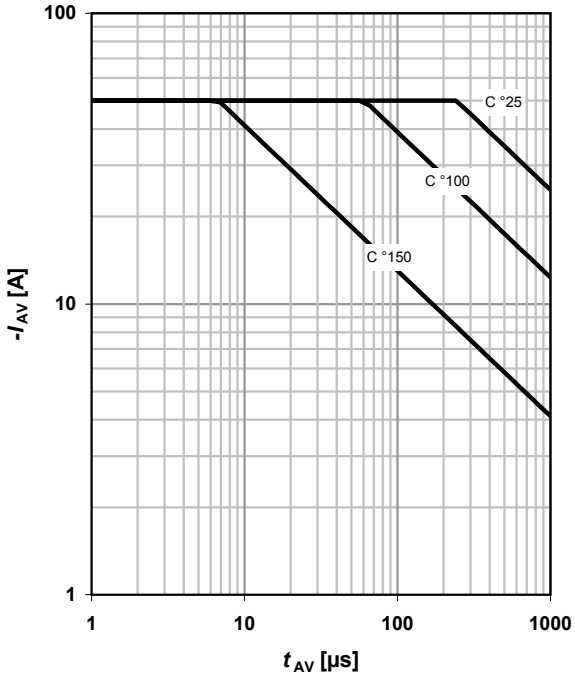
parameter: T_j



13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω

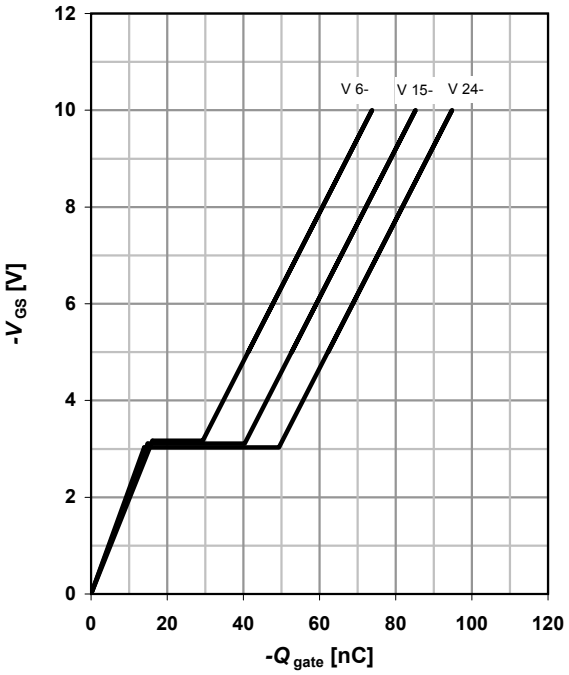
parameter: $T_{j(start)}$



14 Typ. gate charge

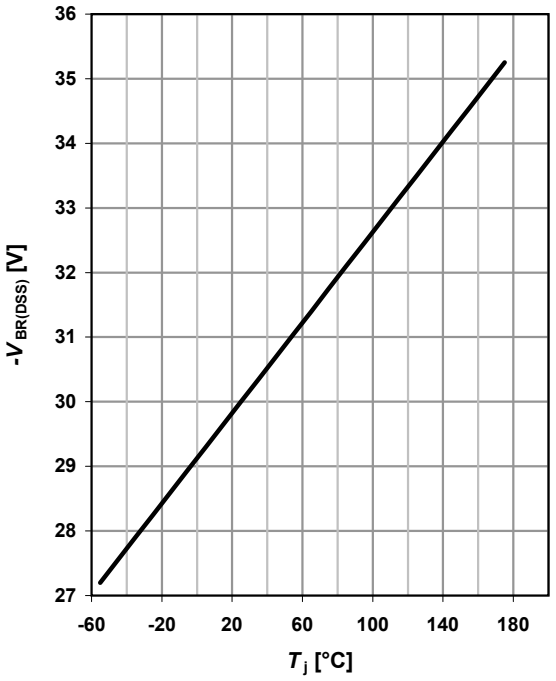
V_{GS}=f(Q_{gate}); I_D=-50 A pulsed

parameter: V_{DD}

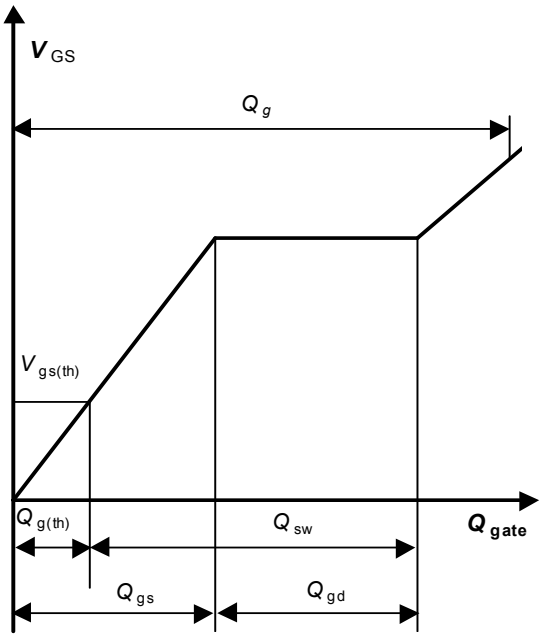


15 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_j); I_D=-250 µA

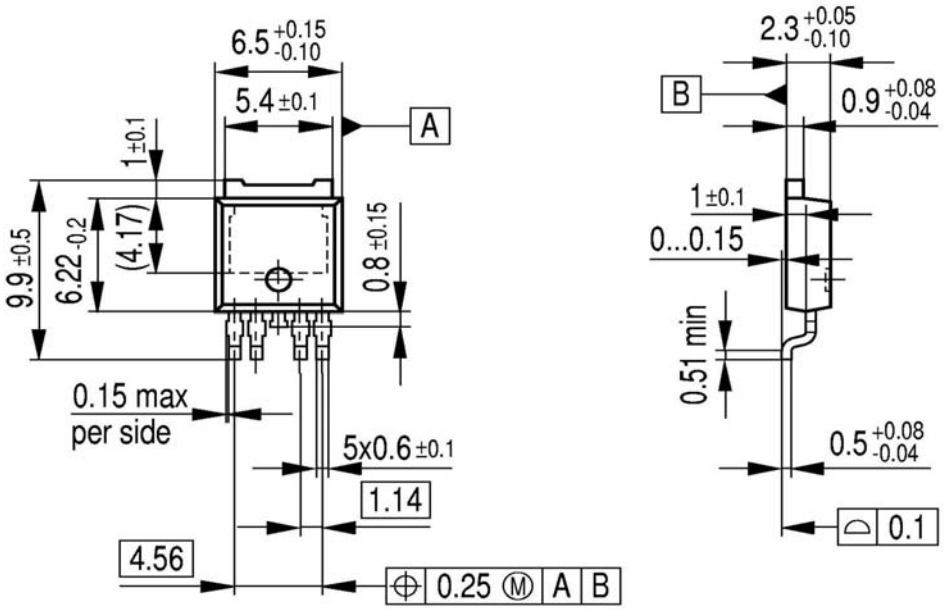


16 Gate charge waveforms

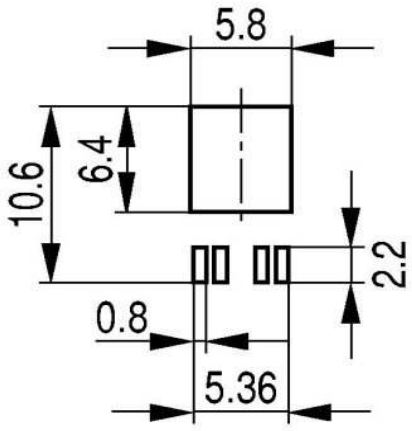


Package Outline

PG-TO252-5: Outline

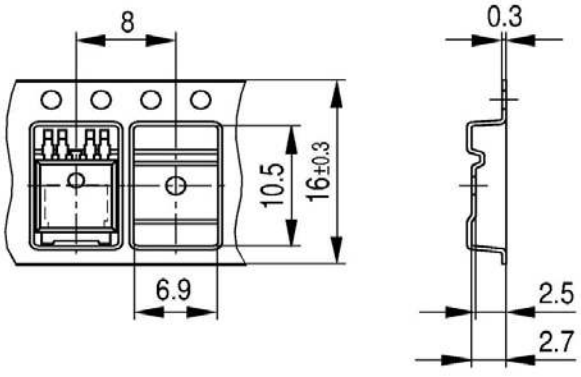


Footprint



Packaging

Tape



Dimensions in mm

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